

**IN THE SPECIFICATION**

Please amend the specification as follows:

**The paragraph beginning at page 1, line 7 is amended as follows:**

This application is related to the following co-pending, commonly assigned U.S. patent applications: "DRAM Cells with Repressed Floating Gate Memory, Low Tunnel Barrier Interpoly Insulators Metal Oxide Tunnel Insulators," attorney docket no. 1303.019US1, serial number 09/945,395, filed August 30, 2001, "Flash Memory with Low Tunnel Barrier Interpoly Insulators," attorney docket no. 1303.014US1, serial number 09/945,507, filed August 30, 2001, "~~Dynamic Electrically Alterable Programmable Memory with Insulating Metal Oxide Interpoly Insulators~~ Integrated Circuit Memory Device and Method," attorney docket no. 1303.024US1, serial number 09/945,498, filed August 30, 2001, and "~~Field In Service Programmable Logic Arrays with Metal Oxide and/or Low Tunnel Barrier Interpoly Insulators~~," attorney docket no. 1303.027US1, serial number 09/945,512, filed August 30, 2001, "SRAM Cells with Repressed Floating Gate Memory, ~~Metal Oxide Tunnel~~ Low Tunnel Barrier Interpoly Insulators," attorney docket no. 1303.028US1, serial number 09/945,554, filed August 30, 2001, "Programmable Memory Address and Decode ~~Devices~~ Circuits with Low Tunnel Barrier Interpoly Insulators," attorney docket no. 1303.029US1, serial number 09/945,500, filed August 30, 2001, of which disclosures are herein incorporated by reference.

**The paragraph beginning at page 38, line 8 is amended as follows:**

For example, results have been obtained which demonstrate that at least a limited range of high temperature, super-conducting oxide films can be made by thermally oxidizing Y-Ba-Cu alloy films (see generally, Hase et al., "Method of manufacturing an oxide superconducting film," U.S. Pat. 5,350,738, Sept. 27, 1994). The present inventors have also disclosed how to employ "low temperature oxidation" and short thermal treatments in an inert ambient at 700 degrees Celsius in order to form a range of perovskite oxide films from parent alloy films (see generally, J. M. Eldridge, "Low Cost Processes for Producing High Quality Perovskite Dielectric Films," application Serial No. \_\_\_\_\_ application Serial No. 09/945,137). The dielectric

A